

# Generic, accurate annual yield calculation for PV modules based on fingerprint method

N.J.J. Dekker\*, M.J. Jansen, J.M. Kroon

ECN Solar Energy



• 2

## PV Efficiency & Annual Yield

PV Power Conversion Efficiency ( $\eta$ )

$$\eta_{\rm STC} = \frac{P_{max}}{A \, Pin}$$

P<sub>max</sub> A P<sub>in</sub>

= max. generated power
= device area
= incident power per m<sup>2</sup> (1000 W/m<sup>2</sup> at STC)

As  $P_{in}$  is well-defined,  $P_{max}$  is reasonably well-defined

$$J = J_{ph} - J_0 \left( e^{\frac{q(V+JR_s)}{nkT}} - 1 \right) + \frac{V + JR_s}{R_{shunt}}$$

$$V_{oc} = \frac{nkT}{q} \ln\left(\frac{J_{Ph}}{J_0} + 1\right)$$

Annual (Electricity) Yield: Y (in kWh)

Specific Yield  $(Y_p)$ 

$$Y_p = \frac{Y}{P_{max}}$$
 (in kWh/W<sub>p</sub>)

Y depends on device efficiency η(S,T,G) &outdoor conditions (T,G):

- $S(\lambda)$ : Spectral response device
- *T* : Temperature
- G<sub>1</sub>(λ,φ,δ): Irradiance (in W/m<sup>2</sup>) specified by:
  - $\circ$  Spectral distribution ( $\lambda$ )
  - Intensity
  - $\circ$  (Angle of incidence ( $\varphi, \delta$ ))



## PV Efficiency & Annual Yield





### PV Efficiency & Annual Yield

#### **PV** Power Conversion Efficiency $(\eta)$

- Relatively easy and fast to determine (see RRs)
- Gives a 'unique' value under steadystate conditions
- Directly correlated to system price (Euro/Wp)

#### Annual (Electricity) Yield:

- Time-consuming to determine
- Strongly depend on location
- Correlated to PV system revenue (kWh produced over lifetime)

#### **Objective:**

To provide a simple and accurate method for calculating the annual yield, based on outdoor IV characteristics of the module ("Fingerprint"), irradiance and ambient temperature data.



## Outdoor test facility in Petten

west

Example A: south oriented Azimuth angle = 170°C



**Example B: facade mounted PV modules** 



Measure simultaneously every 10 minutes:

- IV characteristics: Power output
- T<sub>ambient</sub> and T<sub>module</sub>
- Irradiance (pyranometer and reference cells





### Method

- 1. The irradiance ( $G_i$ ), ambient temperature ( $T_{amb}$ ), module temperature ( $T_{mod}$ ) and power output ( $P_{mpp}$ ) of a module is measured during a limited timeframe
- 2. A "Fingerprint" is made of the module based on these measurements
- **3**. The yearly yield is calculated based on the Fingerprint of the module and annual data set of irradiance and ambient temperature.



## Method





## **Results Fingerprint**

Example of the Fingerprint of wafer based modules (line = model)



#### FP2: Pmpp @25°C vs. Irradiance



## Yield calculation

*Input*: G<sub>i</sub>, T<sub>amb</sub>, FP1, FP2

### Calculated on base of FP:

 $T_{mod} = FP1 (G_i, T_{amb})$  $P_{mpp25} = FP2 (G_i)$ 

Output:

 $P_{mpp} = f (T_{mod}, P_{mpp25}, \gamma_P)$ Yearly Yield

- The input for the annual yield calculation is the irradiance, ambient temperature and the fingerprint relations FP1 and FP2
- From FP1, irradiance and ambient temperature, the module temperature is calculated.
- From FP2 and the irradiance, the temperature corrected power Pmpp25 is calculated.
- The output power Pmpp can be directly calculated from the calculated module temperature and temperature corrected power Pmpp25 and the temperature power coefficient  $\gamma_{\rm P}$ .



### Data analysis

Pmpp(calculated - measured) vs. irradiance

Calculated / measured yield



Module	Yield
ECN-MWT	99.9%
H-pattern	99.9%
a:Si (TJ)	102%



### Conclusions

- The "Fingerprint" method is a simple and accurate method for the calculation of the yearly yield of a module with the irradiance and ambient temperature as input parameters
- Applied for wafer based, inorganic and organic based modules
- The uncertainty can be reduced by adding wind data to the fingerprint calculations of the module temperature, which will reduce the spread of measured and calculated module temperature considerably

Reference:

N.J. Dekker et al . ACCURATE YEARLY YIELD CALCULATION USING PV MODULE FINGERPRINT METHOD APPLIED FOR MWT, H-PATTERN AND THIN FILM MODULES. PROCEEDINGS EUPVSEC, 2016, 5AV 6 40